Oleg Parasyuk

List of Publications by Year in Descending Order

219 papers	3,316 citations	27 h-index	42 g-index
280 ext. papers	3,700 ext. citations	3.8 avg, IF	5.06 L-index

#	Paper	IF	Citations
219	Electronic structure and optical constants of CsPbCl3: The effect of approaches within ab initio calculations in relation to X-ray spectroscopy experiments. *Materials Chemistry and Physics*, **2021**, 261, 124216	4.4	4
218	DFT calculations and experimental studies of the electronic structure and optical properties of Tl4PbI6. *Optical Materials*, **2021**, 114, 110982	3.3	4
217	Quaternary Cu2HgGeSe4 selenide: Its electronic and optical properties as elucidated from TB-mBJ band-structure calculations and XPS and XES measurements. *Chemical Physics*, **2020**, 536, 110821	2.3	5
216	Valence-band electronic structure and main optical properties of Cu2HgGeTe4: Theoretical simulation within a DFT framework and experimental XPS study. *Materials Today Communications*, **2020**, 23, 100828	2.5	4
215	First-principles DFT computation and X-ray spectroscopy study of the electronic band structure and optical constants of Cu2HgGeS4. *Solid State Sciences*, **2020**, 104, 106287	3.4	7
214	Simulation within a DFT framework and experimental study of the valence-band electronic structure and optical properties of quaternary selenide Cu2HgSnSe4. *Optik*, **2020**, 202, 163709	2.5	6
213	New cation-disordered quaternary selenides Tl2Ga2TtSe6 (Tt=Ge, Sn). *Zeitschrift Fur Naturforschung - Section B Journal of Chemical Sciences*, **2020**, 75, 135-142	1	4
212	Calculations within DFT framework of the electronic and optical properties of quaternary sulfide Tl2PbSiS4, a prospective optoelectronic semiconductor. *Computational Condensed Matter*, **2019**, 21, e00392	1.7	7
211	Electronic and optical properties of quaternary sulfide Tl2HgSnS4, a promising optoelectronic semiconductor: A combined experimental and theoretical study. *Optical Materials*, **2019**, 92, 294-302	3.3	6
210	Preparation, electronic structure and piezooptical properties of solid solutions Tl3PbBr5 *Materials Chemistry and Physics*, **2019**, 227, 255-264	4.4	1
209	A theoretical and experimental study of the valence-band electronic structure and optical constants of quaternary copper mercury tin sulfide, Cu2HgSnS4, a potential material for optoelectronics and solar cells. *Optical Materials*, **2019**, 96, 109296	3.3	23
208	Electronic band structure and basic optical constants of TlGaSn2Se6, a promising NLO semiconductor: First-principles calculations under DFT framework. *Optik*, **2019**, 181, 673-685	2.5	9
207	Electronic, Optical and Elastic Properties of Cu2CdGeSe4: A First-Principles Study. *Journal of Electronic Materials*, **2019**, 48, 705-715	1.9	10
206	The effect of composition on photoconductivity and nonlinear optical properties in the acentric Ag2In2AB6 (A = Si, Ge, B = S, Se) crystals. *Optik*, **2019**, 179, 948-956	2.5	2
205	Particular features of the electronic structure and optical properties of Ag2PbGeS4 as evidenced from first-principles DFT calculations and XPS studies. *Materials Chemistry and Physics*, **2018**, 208, 268-280	4.4	23
204	PbGa2GeS6 crystal as a novel nonlinear optical material: Band structure aspects. *Journal of Alloys and Compounds*, **2018**, 740, 294-304	5.7	20
203	Electronic structure and optical properties of Ag2HgSnSe4: First-principles DFT calculations and X-ray spectroscopy studies. *Journal of Alloys and Compounds*, **2018**, 732, 372-384	5.7	40

202	Electronic structure and laser induced piezoelectricity of a new quaternary compound TlInGe3S8. *Materials Chemistry and Physics*, **2018**, 204, 336-344	4.4	12
201	Photoconductivity and laser operated piezoelectricity the Ag-Ga-Ge-(S,Se) crystals and solid solutions. *Materials Science in Semiconductor Processing*, **2018**, 86, 101-110	4.3	4
200	Electronic band-structure and optical constants of Pb2GeS4: Ab initio calculations and X-ray spectroscopy experiments. *Journal of Materials Science: Materials in Electronics*, **2018**, 29, 16088-16100	2.1	4
199	First-principles DFT calculations of the electronic structure and optical properties of TlInGe2Se6, a prospective NLO material. *Materials Chemistry and Physics*, **2018**, 219, 162-174	4.4	11
198	Experimental and theoretical study of Raman scattering spectra of ternary chalcogenides Tl4HgI6, Tl4HgBr6, and TlHgCl3. *Journal of Raman Spectroscopy*, **2018**, 49, 1840-1848	2.3	6
197	Thallium indium germanium sulphide (TlInGe2S6) as efficient material for nonlinear optical application. *Journal of Alloys and Compounds*, **2018**, 735, 1694-1702	5.7	10
196	Electronic structure and optical properties of defect chalcopyrite HgGa2Se4. *Optical Materials*, **2018**, 75, 538-546	3.3	6
195	Raman Scattering Study of Mixed Quaternary AgxGaxGe1−xSe2 (0.167 ≤ x ≤ 0.333) Crystals. *Physica Status Solidi (B): Basic Research*, **2018**, 255, 1700230	1.3	3
194	Electronic structure and basic optical constants of TlHgBr3: Density functional theory calculations. *Optical Materials*, **2018**, 86, 191-197	3.3	5
193	TlInGe2S6, A Prospective Nonlinear Optical Material: First-Principles DFT Calculations of the Electronic Structure and Optical Properties. *Journal of Electronic Materials*, **2018**, 47, 5525-5536	1.9	11
192	Specific features of photoconductivity and photoinduced piezoelectricity in AgGaGe 3 Se 8 doped crystals. *Optical Materials*, **2017**, 63, 197-206	3.3	9
191	Vibrational spectroscopy of orthorhombic Cu2ZnSiS4 single crystal: Low-temperature polarized Raman scattering and first principle calculations. *Vibrational Spectroscopy*, **2017**, 89, 81-84	2.1	4
190	Optical absorption, piezoelectric effect and second harmonic generation studies of single crystal AgGaGe3Se7.6Te0.4 solid solution. *Applied Physics A: Materials Science and Processing*, **2017**, 123, 1	2.6	4
189	The Tl2SPbSSiS2 system and the crystal and electronic structure of quaternary chalcogenide Tl2PbSiS4. *Materials Chemistry and Physics*, **2017**, 195, 132-142	4.4	5
188	Synthesis, structural, X-ray photoelectron spectroscopy (XPS) studies and IR induced anisotropy of Tl4HgI6 single crystals. *Materials Chemistry and Physics*, **2017**, 187, 156-163	4.4	14
187	Synthesis, electronic structure and optical properties of PbBr 1.2 I 0.8. *Journal of Electron Spectroscopy and Related Phenomena*, **2017**, 218, 13-20	1.7	2
186	Two-photon absorption of Tl1-xIn1-xSnxSe2nanocrystallites. *EPJ Web of Conferences*, **2017**, 133, 03001	0.3	
185	Synthesis, structural, electronic and linear electro-optical features of new quaternary Ag2Ga2SiS6 compound. *Journal of Solid State Chemistry*, **2017**, 246, 363-371	3.3	10

184	Tl2SGa2S3GeS2 glasses for optically operated laser third harmonic generation. *Journal of Materials Science: Materials in Electronics*, **2017**, 28, 19003-19009	2.1	5
183	AgGaSiSe4: Growth, crystal and band electronic structure, optoelectronic and piezoelectric properties. *Materials Research Bulletin*, **2017**, 95, 177-184	5.1	3
182	Photoconductivity relaxation processes in AgCd2GaS4 single crystals. *Materials Chemistry and Physics*, **2017**, 200, 250-256	4.4	1
181	New quaternary thallium indium germanium selenide TlInGe2Se6: Crystal and electronic structure. *Journal of Solid State Chemistry*, **2017**, 254, 103-108	3.3	8
180	Photoconductivity and nonlinear optical features of novel Ag x Ga x Ge 1-x Se 2 crystals. *Materials Research Bulletin*, **2017**, 85, 74-79	5.1	15
179	Tl10Hg3Cl16: Single crystal growth, electronic structure and piezoelectric properties. *Journal of Solid State Chemistry*, **2016**, 242, 193-198	3.3	8
178	Experimental and theoretical study of the electronic structure and optical spectral features of PbIn6Te10. *RSC Advances*, **2016**, 6, 73107-73117	3.7	5
177	Novel AgGa 0.95 In 0.05 Ge 3 Se 8 crystalline alloys for light-operated piezoelectricity. *Journal of Alloys and Compounds*, **2016**, 658, 408-413	5.7	11
176	Huge operation by energy gap of novel narrow band gap Tl1−In1−BxSe2(B = Si, Ge): DFT, x-ray emission and photoconductivity studies. *Materials Research Express*, **2016**, 3, 025902	1.7	14
175	Single crystal growth and electronic structure of TlPbI3. *Materials Chemistry and Physics*, **2016**, 172, 165-172	4.1	31
174	Influence of Cu-, Sn-, and In-Doping on Optical Properties of AgGaGe3 Se8 Single Crystals. *Ukrainian Journal of Physics*, **2016**, 61, 606-612	0.4	
173	A Novel Effect of CO2 Laser Induced Piezoelectricity in Ag2Ga2SiS6 Chalcogenide Crystals. *Crystals*, **2016**, 6, 107	2.3	5
172	Crystal structure and vibrational properties of Cu2ZnSiSe4 quaternary semiconductor. *Physica Status Solidi (B): Basic Research*, **2016**, 253, 1808-1815	1.3	17
171	Laser operated piezoelectricity in Ag0.5Pb1.75GeS4 and Ag0.5Pb1.75GeS3Se crystals. *Journal of Materials Science: Materials in Electronics*, **2016**, 27, 9589-9592	2.1	3
170	Enhanced persistent photoconduction in CuInS2ZnIn2S4 alloys single crystals and processes of its relaxation. *Molecular Crystals and Liquid Crystals*, **2016**, 627, 153-162	0.5	1
169	Synthesis and structure of novel Ag2Ga2SiSe6 crystals: promising materials for dynamic holographic image recording. *RSC Advances*, **2016**, 6, 90958-90966	3.7	13
168	Manifestation of Anomalous Weak Space-Charge-Density Acentricity for a TlHgBr Single Crystal. *Inorganic Chemistry*, **2016**, 55, 10547-10557	5.1	16
167	Electronic structure and optical properties of Cs2HgCl4: DFT calculations and X-ray photoelectron spectroscopy measurements. *Optical Materials*, **2016**, 60, 169-180	3.3	7

166	Electrical properties and electronic structure of Cu1−ZnxInSe2 and Cu1−ZnxInS2 single crystals. *Journal of Physics and Chemistry of Solids*, **2015**, 82, 42-49	3.9	3
165	The electronic structure of defect chalcopyrite CdGa2Se4 as determined from first principles calculations and X-ray spectroscopy studies. *Journal of Structural Chemistry*, **2015**, 56, 492-496	0.9	6
164	Photoconductivity relaxation processes in Cu1−ZnxInS2 solid solutions. *Materials Science in Semiconductor Processing*, **2015**, 39, 665-670	4.3	2
163	Electronic structure and optical properties of Cu2CdGeS4: DFT calculations and X-ray spectroscopy measurements. *Optical Materials*, **2015**, 47, 435-444	3.3	22
162	Electronic structure of Cu2CdGeSe4 single crystal as determined from X-ray spectroscopy data. *Materials Chemistry and Physics*, **2015**, 160, 345-351	4.4	21
161	Photoinduced Optical Properties Of Tl1−In1−SixSe2 Single Crystals. *Archives of Metallurgy and Materials*, **2015**, 60, 1051-1055		2
160	Growth, structure and optical properties of Tl4HgBr6 single crystals. *Physica B: Condensed Matter*, **2015**, 479, 134-142	2.8	14
159	Single crystal growth, structure and properties of TlHgBr3. *Optical Materials*, **2015**, 49, 94-99	3.3	11
158	Growth of AgGaGe3−SnxSe8 single crystals with light-operated piezoelectricity. *Materials Letters*, **2015**, 161, 705-707	3.3	6
157	Influence of cation-vacancy defects on the properties of CuInSe2−ZnIn2Se4 solid solutions. *Journal of Alloys and Compounds*, **2015**, 618, 712-717	5.7	7
156	Optically stimulated IR non-linear optical effects in the Tl3PbCl5 nanocrystallites. *Physica E: Low-Dimensional Systems and Nanostructures*, **2015**, 65, 130-134	3	5
155	Single crystal growth, electronic structure and optical properties of Cs2HgBr4. *Journal of Physics and Chemistry of Solids*, **2015**, 85, 254-263	3.9	12
154	Growth and Analysis of Nanostructured CuInSe2-ZnIn2Se4 Solid Solutions: Their Electrical and Photoelectrical Properties. *Materials Today: Proceedings*, **2015**, 2, 178-192	1.4	1
153	Transport Phenomena In Single Crystals Tl1−In1−GeXSe2 (x=0.1, 0.2). *Archives of Metallurgy and Materials*, **2015**, 60, 2025-2028		
152	Electronic structure of Cu2ZnGeSe4 single crystal: Ab initio FP-LAPW calculations and X-ray spectroscopy measurements. *Physica B: Condensed Matter*, **2015**, 461, 75-84	2.8	46
151	Electronic structure and optical properties of Cs2HgI4: Experimental study and band-structure DFT calculations. *Optical Materials*, **2015**, 42, 351-360	3.3	23
150	Origin of electronic properties of PbGa2Se4 crystal: Experimental and theoretical investigations. *Journal of Alloys and Compounds*, **2015**, 633, 415-423	5.7	12
149	Solid-state solutions of copper indium disulfide and zinc indium tetrasulfide: Growth, crystallography and opto-electronic properties. *Materials Science in Semiconductor Processing*, **2014**, 24, 231-236	4.3	1

148	X-ray spectroscopy study of the electronic structure of non-centrosymmetric Ag2CdSnS4 single crystal. *Optical Materials*, **2014**, 36, 1396-1401	3.3	23
147	Specific features of the electronic structure of a novel ternary Tl3PbI5 optoelectronic material. *Physical Chemistry Chemical Physics*, **2014**, 16, 12838-47	3.6	18
146	Origin of anisotropy of the near band gap absorption in Tl4HgBr6 single crystals. *Journal of Materials Chemistry C*, **2014**, 2, 2779	7.1	7
145	Electronic structure of non-centrosymmetric Ag2HgSnS4 single crystal. *Optical Materials*, **2014**, 36, 977-981	3.3	22
144	Optoelectronic features of novel infrared CuInS2–ZnIn2S4 crystalline alloys. *Journal of Materials Science: Materials in Electronics*, **2014**, 25, 163-167	2.1	8
143	Electronic structure and photoelectrical properties of Ag2In2SiSe6 and Ag2In2GeSe6. *Optical Materials*, **2014**, 38, 10-16	3.3	17
142	Manifestation of intrinsic defects in the band structures of quaternary chalcogenide Ag2In2SiSe6 and Ag2In2GeSe6 crystals. *CrystEngComm*, **2014**, 16, 9534-9544	3.3	7
141	Structural and optical features of novel Tl1–In1–GexSe2 chalcogenide crystals. *Optical Materials*, **2014**, 37, 614-620	3.3	5
140	Electronic structure, optical properties, and lattice dynamics of orthorhombic Cu2CdGeS4 and Cu2CdSiS4 semiconductors. *Physical Review B*, **2014**, 90,	3.3	28
139	Specific features of band structure and optical anisotropy of Cu2CdGeSe4 quaternary compounds. *Materials Chemistry and Physics*, **2014**, 147, 155-161	4.4	17
138	Influence of cation-vacancy imperfection on the electrical and photoelectric properties of the Cu1 − x Zn x InS2 alloy. *Semiconductors*, **2014**, 48, 286-291	0.7	2
137	Specific features of the low-temperature conductivity and photoconductivity of CuInSe2-ZnIn2Se4 alloys. *Semiconductors*, **2014**, 48, 727-732	0.7	2
136	Structural and optical properties of novel optoelectronic Tl1–In1–SixSe2 single crystals. *Journal of Materials Science: Materials in Electronics*, **2014**, 25, 3226-3232	2.1	9
135	CuInS2-ZnIn2S4 Solid Solutions: Growth, Physical and Photo-electrical Properties. *Molecular Crystals and Liquid Crystals*, **2014**, 604, 164-173	0.5	
134	First-principles band-structure calculations and X-ray photoelectron spectroscopy studies of the electronic structure of TlPb2Cl5. *Journal of Alloys and Compounds*, **2014**, 582, 802-809	5.7	23
133	IR laser induced spectral kinetics of AgGaGe3Se8:Cu chalcogenide crystals. *Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy*, **2013**, 111, 142-9	4.4	10
132	Electronic and optical features of the mixed crystals Ag0.5Pb1.75Ge(S1–Sex)4. *Journal of Materials Chemistry C*, **2013**, 1, 4667	7.1	9
131	Two-photon absorption of Tl1–In1–SnxSe2 (x = 0, 0.1, 0.2, 0.25) single crystalline alloys and their nanocrystallites. *Optical Materials*, **2013**, 35, 2514-2518	3.3	14

130	Photoinduced features of energy bandgap in quaternary Cu2CdGeS4 crystals. *Journal of Physics Condensed Matter*, **2013**, 25, 505802	1.8	14
129	Optical spectra and band structure of Ag(x)Ga(x)Ge(1-x)Se2 (x = 0.333, 0.250, 0.200, 0.167) single crystals: experiment and theory. *Journal of Physical Chemistry B*, **2013**, 117, 15220-31	3.4	33
128	Single crystal growth and the electronic structure of TlPb2Br5. *Optical Materials*, **2013**, 36, 251-258	3.3	22
127	Linear, non-linear optical susceptibilities and the hyperpolarizability of the mixed crystals Ag(0.5)Pb(1.75)Ge(S(1-x)Se(x))4: experiment and theory. *Physical Chemistry Chemical Physics*, **2013**, 15, 18979-86	3.6	144
126	Formation of intermediate solid solutions in the quaternary exchange system Cu(In,Ga)(S,Se)2–Cd(S,Se). *CrystEngComm*, **2013**, 15, 4838	3.3	22
125	X-ray photoelectron spectrum, X-ray diffraction data, and electronic structure of chalcogenide quaternary sulfide Ag2In2GeS6: experiment and theory. *Journal of Materials Science*, **2013**, 48, 1342-1350	4.3	20
124	Electrical and photoelectrical properties of CuInS2–InIn2S4 solid solutions. *Journal of Alloys and Compounds*, **2013**, 553, 48-52	5.7	13
123	Influence of replacing Si by Ge in the chalcogenide quaternary sulfides Ag2In2Si(Ge)S6 on the chemical bonding, linear and nonlinear optical susceptibilities, and hyperpolarizability. *Journal of Physical Chemistry B*, **2013**, 117, 2545-53	3.4	35
122	IR laser induced spectra in novel crystals CdTe-CuInTe2. *Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy*, **2013**, 116, 446-50	4.4	1
121	Single crystal growth and the electronic structure of orthorhombic Tl3PbBr5: A novel material for non-linear optics. *Optical Materials*, **2013**, 35, 1081-1089	3.3	32
120	Photoelectrical properties and the electronic structure of Tl(1-x)In(1-x)Sn(x)Se2 (x = 0, 0.1, 0.2, 0.25) single crystalline alloys. *Physical Chemistry Chemical Physics*, **2013**, 15, 6965-72	3.6	156
119	Second anion coordination for wurtzite and sphalerite chalcogenide derivatives as a tool for the description of anion sub-lattice. *Materials Chemistry and Physics*, **2013**, 139, 92-99	4.4	31
118	The crystal structure of novel silver sulphogermanate Ag10Ge3S11. *Journal of Alloys and Compounds*, **2013**, 576, 134-139	5.7	0
117	Electronic structure of the high-temperature tetragonal Tl3PbBr5 phase. *Journal of Alloys and Compounds*, **2013**, 576, 271-278	5.7	20
116	Laser-induced piezoelectric effects in chalcogenide crystals. *Physica B: Condensed Matter*, **2013**, 423, 60-63	2.8	11
115	Photothermal poling of glass complexes Ag2S–Ga2S3–P2S5. *Optics Communications*, **2013**, 307, 1-4	2	7
114	Spectral and conductivity features of novel ternary Tl1–xIn1–xSnxS2 crystals. *Crystal Research and Technology*, **2013**, 48, 464-475	1.3	8
113	Photo induced anisotropy in the AgGaGe3Se8:Cu chalcogenide crystals. *Materials Letters*, **2013**, 107, 218-220	3.3	13

112	Tl1−xIn1−xSnxSe2 (x = 0, 0.1, 0.2, 0.25) single-crystalline alloys as promising non-linear optical materials. *Journal of Materials Science: Materials in Electronics*, **2013**, 24, 3555-3563	2.1	20
111	Electronic Structure of Quaternary Chalcogenide Ag2In2Ge(Si)S6 Single Crystals and the Influence of Replacing Ge by Si: Experimental X-Ray Photoelectron Spectroscopy and X-Ray Diffraction Studies and Theoretical Calculations. *Science of Advanced Materials*, **2013**, 5, 316-327	2.3	40
110	IR-induced features of AgGaGeS4 crystalline semiconductors. *Journal of Physics and Chemistry of Solids*, **2012**, 73, 439-443	3.9	10
109	Influence of technological defects on the optical and photoelectric properties of AgCd2 −x Mn x GaSe4 alloys. *Semiconductors*, **2012**, 46, 306-311	0.7	
108	Physico-chemical interaction in the Tl2Se–HgSe–DIVSe2 systems (DIV – Si, Sn). *Materials Research Bulletin*, **2012**, 47, 3830-3834	5.1	8
107	Synthesis and spectral features of Ag2SnS3 crystals. *Materials Chemistry and Physics*, **2012**, 135, 249-253	4.4	10
106	Electronic spectral parameters and IR nonlinear optical features of novel Ag0.5Pb1.75GeS4 crystal. *Journal of Crystal Growth*, **2012**, 354, 142-146	1.6	46
105	Electronic structure of non-centrosymmetric AgCd2GaS4 and AgCd2GaSe4 single crystals. *Journal of Electron Spectroscopy and Related Phenomena*, **2012**, 185, 559-566	1.7	40
104	Crystal growth, electron structure and photo induced optical changes in novel AgxGaxGe1−xSe2 (x=0.333, 0.250, 0.200, 0.167) crystals. *Optical Materials*, **2012**, 35, 65-73	3.3	44
103	Photovoltaic, photoelectric and optical spectra of novel AgxGaxGe1−xSe2 (0.167 ≤ x ≤ 0.333) quaternary single crystals. *Materials Chemistry and Physics*, **2012**, 135, 837-841	4.4	16
102	Soft-mode-driven lattice instabilities in Cs2HgCl4 crystal: phenomenological treatment and far-infrared spectroscopy of the structurally modulated phases. *Journal of Physics Condensed Matter*, **2012**, 24, 245901	1.8	3
101	Phase equilibria in the Tl2S–PbS–GeS2 system and crystal structure of Tl0.5Pb1.75GeS4. *Chemistry of Metals and Alloys*, **2012**, 5, 37-41	1	2
100	Phase diagram of the quasi-binary system TlInSe2–SnSe2. *Journal of Alloys and Compounds*, **2011**, 509, 2693-2696	5.7	15
99	Growth and properties of the single AgCd2GaSe4 crystals. *Journal of Crystal Growth*, **2011**, 330, 5-8	1.6	6
98	IR operated novel Ag0.98Cu0.02GaGe3Se8 single crystals. *Journal of Physics and Chemistry of Solids*, **2011**, 72, 1354-1357	3.9	28
97	Synthesis and structural properties of CuInGeS4. *Journal of Crystal Growth*, **2011**, 324, 212-216	1.6	30
96	Ag2HgSnS4 single crystals as promising materials for optoelectronic. *Optical Materials*, **2011**, 33, 1302-1306	3.3	35
95	Crystal growth and the electronic structure of Tl3PbCl5. *Journal of Physics and Chemistry of Solids*, **2011**, 72, 705-713	3.9	36

94	Single crystal preparation and properties of the AgGaGeS4–AgGaGe3Se8 solid solution. *Journal of Crystal Growth*, **2011**, 318, 708-712	1.6	29
93	The CuGaSe2–CuInSe2–CdS system and single crystal growth of the δ-phase. *Journal of Crystal Growth*, **2011**, 318, 332-336	1.6	7
92	Phase equilibria in the systems AgInSe2-HgIn2Se4 and AgInSe2-HgSe. *Inorganic Materials*, **2010**, 46, 609-613	0.9	
91	Quasi-ternary system CuGaS2–CuInS2–CdS. *Journal of Alloys and Compounds*, **2010**, 492, 184-189	5.7	7
90	The Ag2S–ZnS–GeS2 system: Phase diagram, glass-formation region and crystal structure of Ag2ZnGeS4. *Journal of Alloys and Compounds*, **2010**, 500, 26-29	5.7	26
89	Crystal structure of the phases Hg5CIII2X8 (CIII = Ga, In; X = Se, Te). *Journal of Alloys and Compounds*, **2010**, 503, 40-43	5.7	25
88	The CuInSe2–CuGaSe2–CdSe system and crystal growth of the δ-solid solutions. *Journal of Alloys and Compounds*, **2010**, 505, 101-107	5.7	6
87	Concentration dependence of the optical properties of glassy alloys in the HgS-Ga2S3-GeS2 system. *Glass Physics and Chemistry*, **2010**, 36, 27-32	0.7	11
86	Piezooptical coefficients of La3Ga5SiO14 and CaWO4 crystals: A combined optical interferometry and polarization-optical study. *Optical Materials*, **2010**, 33, 26-30	3.3	19
85	The reciprocal system CuGaS2+CuInSe2DCuGaSe2+CuInS2. *Chemistry of Metals and Alloys*, **2010**, 3, 18-231		5
84	Single crystal growth and properties of the δ-phase in the CuInSe2–CdTe system. *Journal of Crystal Growth*, **2009**, 311, 2381-2384	1.6	14
83	The reciprocal system Cu2GeS3+3CdSe<=>Cu2GeSe3+3CdS. *Journal of Alloys and Compounds*, **2009**, 473, 94-99	5.7	9
82	Phase equilibria in the quasi-ternary system Ag2S–In2S3–CdS at 870 K. *Journal of Alloys and Compounds*, **2009**, 480, 360-364	5.7	5
81	Electronic structure of cadmium selenogallate CdGa2Se4 as studied using ab initio calculations and X-ray photoelectron spectroscopy. *Journal of Alloys and Compounds*, **2009**, 481, 28-34	5.7	38
80	Quasi-ternary system Cu2GeS3–Cu2SnS3–CdS. *Journal of Alloys and Compounds*, **2009**, 484, 147-153	5.7	10
79	Glass formation and optical properties of the glasses in the Ag2S–HgS–GeS2 system. *Chemistry of Metals and Alloys*, **2009**, 2, 49-54	1	4
78	Effect of doping with transition and rare-earth metals on the electrical and optical properties of AgGaGe3Se8 single crystals. *Inorganic Materials*, **2008**, 44, 361-365	0.9	5
77	The Ag2S–In2S3–Si(Ge)S2 systems and crystal structure of quaternary sulfides Ag2In2Si(Ge)S6. *Journal of Alloys and Compounds*, **2008**, 452, 348-358	5.7	45

76	The CdSe–Ga2Se3–PbSe system. *Journal of Alloys and Compounds*, **2008**, 453, 115-120	5.7	2
75	AgCrTiS4: Synthesis, Properties, and Analytical Application. *Metallurgical and Materials Transactions B: Process Metallurgy and Materials Processing Science*, **2008**, 39, 155-159	2.5	2
74	Quaternary thiospinel CuCrTiS4 as an electroactive material for copper(II)-sensitive and selective electrode. *Materials Science and Engineering C*, **2008**, 28, 1112-1116	8.3	3
73	Single crystal growth and properties of β-phase in the CuInSe2+2CdS<=>CuInS2+2CdSe reciprocal system. *Solar Energy Materials and Solar Cells*, **2008**, 92, 1495-1499	6.4	15
72	Optical and photoelectrical properties of AgCd2GaS4 single-crystal compounds. *Semiconductors*, **2008**, 42, 508-513	0.7	3
71	Crystal structure of the new quaternary copper manganese and zirconium chalcogenides. *Physica Status Solidi (B): Basic Research*, **2007**, 244, 1288-1295	1.3	1
70	New compounds Cu2MnTi3S8 and Cu2NiTi3S8 with thiospinel structure. *Materials Research Bulletin*, **2007**, 42, 143-148	5.1	10
69	The system Ag2Se–Ho2Se3 in the 0–50 mol.% Ho2Se3 range and the crystal structure of two polymorphic forms of AgHoSe2. *Materials Research Bulletin*, **2007**, 42, 1091-1098	5.1	6
68	ELECTRONIC STRUCTURE OF AgCd2GaS4. *Surface Review and Letters*, **2007**, 14, 403-409	1.1	18
67	Formation of an endothermal Cu2In2SiS6 compound in the CuInS2–SiS2 system. *Journal of Alloys and Compounds*, **2007**, 443, 61-67	5.7	14
66	Sellmeier equations for green, yellow, and orange colored HgGa2S4 crystals. *Applied Physics Letters*, **2007**, 90, 181913	3.4	15
65	Synthesis and X-ray powder diffraction studies of semiconducting alloys in the system AgCd2-xZnxGaS4. *Crystal Research and Technology*, **2006**, 41, 32-36	1.3	3
64	X-ray powder diffraction refinement of Ag2In2SiSe6 structure and phase diagram of the AgInSe2–SiSe2 system. *Journal of Alloys and Compounds*, **2006**, 414, 73-77	5.7	14
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